



No.1879B

DTM 8-N

Silicon Planar Type

8A Bidirectional Thyristor

Features

- Insulation type
- Peak OFF-state voltage : 200 to 600V
- RMS ON-state current : 8A
- TO-220 package

Absolute Maximum Ratings at Ta = 25°C

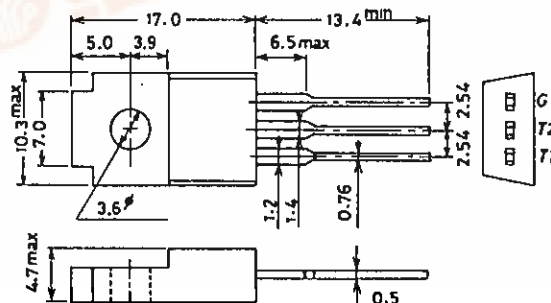
			CDTM 8C-N	DTM 8E-N	DTM 8G-N	unit
Repetitive Peak OFF-State Voltage	V_{DRM}		200	400	600	V
RMS ON-State Current	$I_{T(RMS)}$	$T_c = 83^\circ\text{C}$, single-phase full-wave	→	→	8	A
Surge ON-State Current	I_{TSM}	Peak 1 cycle, 50Hz	→	→	80	A
Amperes Squared-Seconds	$i^2t\text{-}dt$	$1\text{ms} \leq t \leq 10\text{ms}$	→	→	32	A ² S
Peak Gate Power Dissipation	P_{GM}	$f \geq 50\text{Hz}$, duty $\leq 10\%$	→	→	5	W
Average Gate Power Dissipation	$P_{G(AV)}$		→	→	0.5	W
Peak Gate Current	I_{GM}	$f \geq 50\text{Hz}$, duty $\leq 10\%$	→	→	± 2	A
Peak Gate Voltage	V_{GM}	$f \geq 50\text{Hz}$, duty $\leq 10\%$	→	→	± 10	V
Junction Temperature	T_j		→	→	125	°C
Storage Temperature	T_{stg}		→	-40 to +125		°C
Weight			→	→	2.1	g

Electrical Characteristics at Ta = 25°C

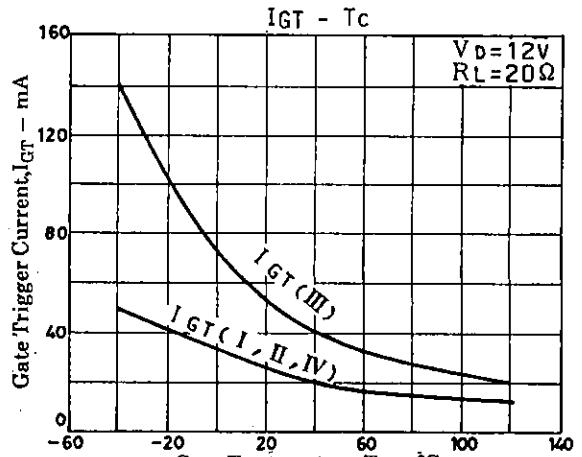
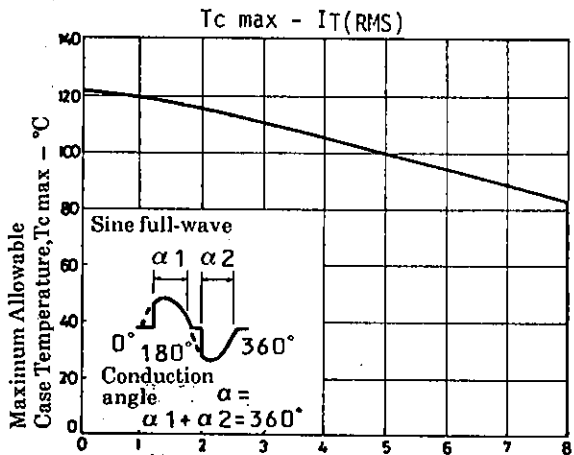
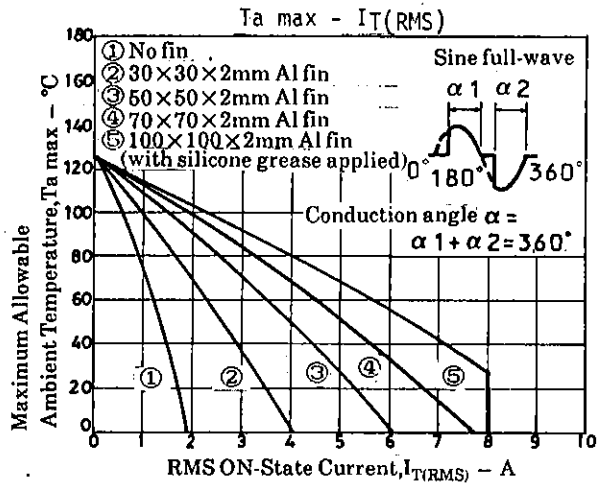
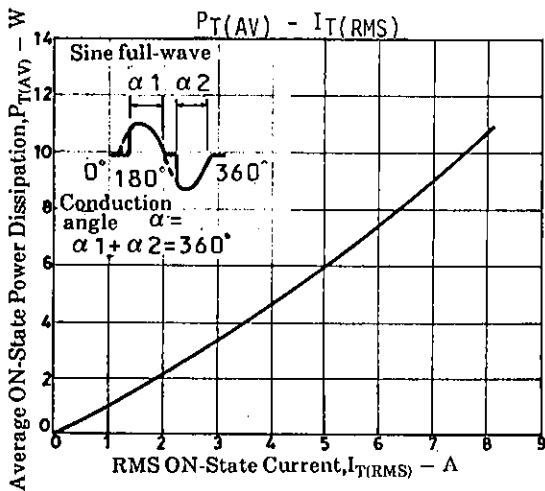
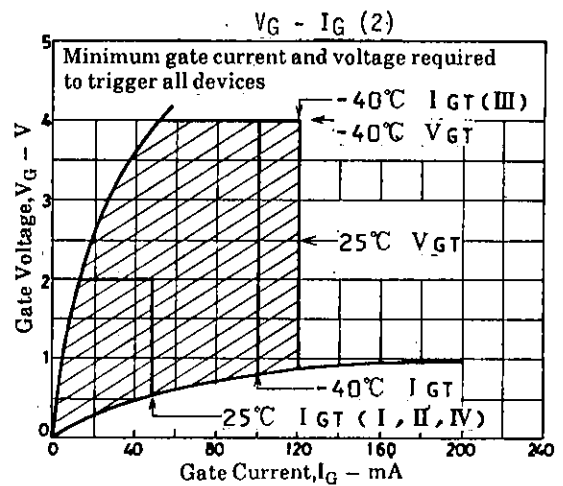
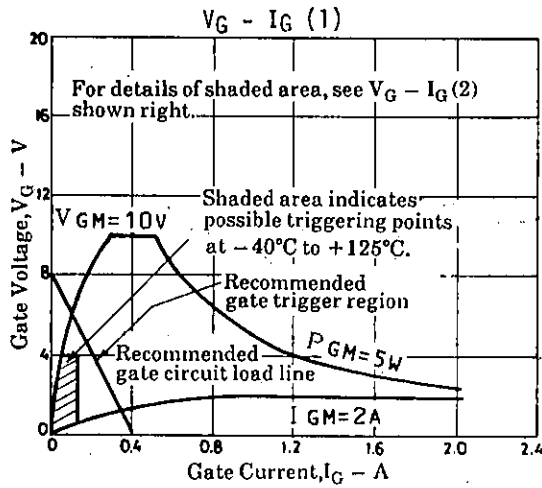
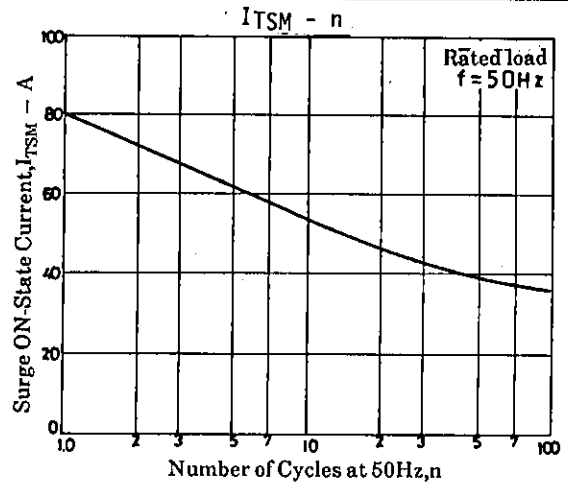
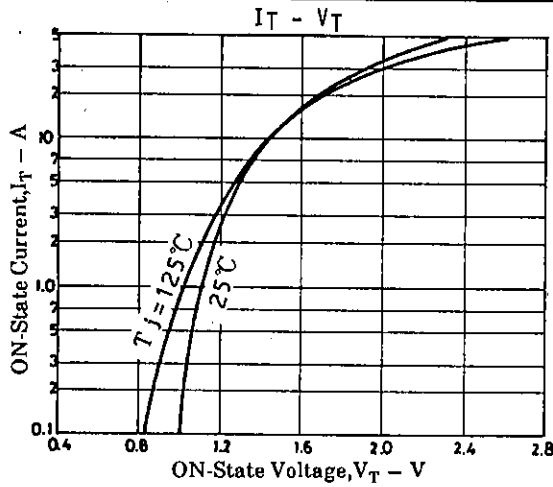
			min	typ	max	unit
Repetitive Peak OFF-State Current	I_{DRM}	$T_j = 125^\circ\text{C}$, $V_D = V_{DRM}$			2	mA
Peak ON-State Voltage	V_{TM}	$I_{TM} = 12\text{A}$			1.5	V
Critical Rate of Rise of OFF-State Voltage	$(dv/dt)_c$	$T_j = 125^\circ\text{C}$, $V_D = 200\text{V(C)}$, 400V(E to G)	10			V/ μs
Holding Current	I_H	$R_L = 100\Omega$			50	mA
Gate Trigger Current※ (I)	I_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			30	mA
	(II) I_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			30	mA
	(III) I_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			50	mA
	(IV) I_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			30	mA
Gate Trigger Voltage※ (I)	V_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			2	V
	(II) V_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			2	V
	(III) V_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			2	V
	(IV) V_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			2	V
Gate Nontrigger Voltage	V_{GD}	$T_c = 125^\circ\text{C}$, $V_D = V_{DRM}$	0.2			V
Thermal Resistance	$R_{th(j-c)}$	Between junction and case, AC			3.6	°C/W

※ : The gate trigger mode is shown below. **Package Dimensions 1144**
(unit: mm)

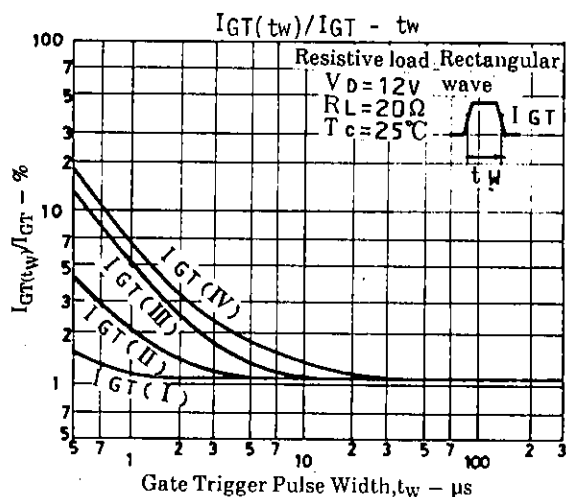
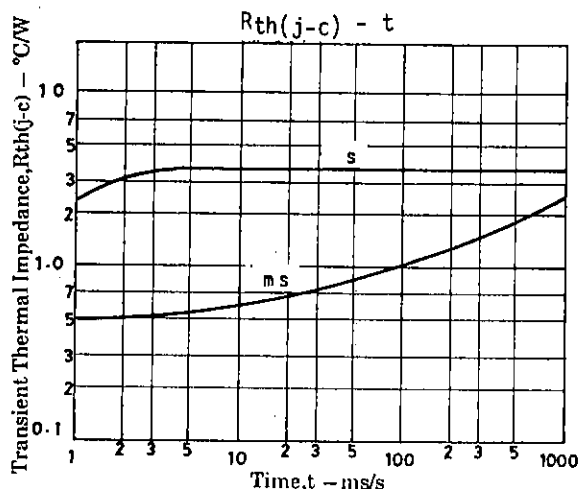
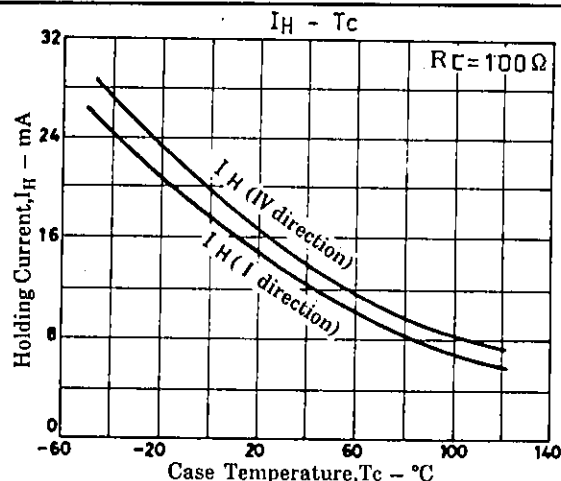
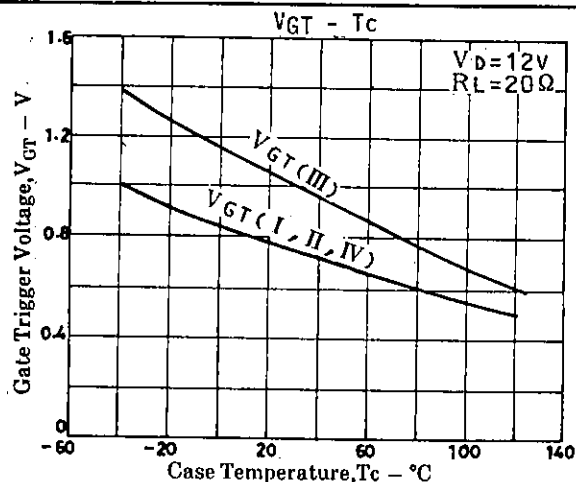
Trigger mode	T2	T1	G
I	+	-	+
II	+	-	-
III	-	+	+
IV	-	+	-



DTM8-N



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